

### P6SMB-E Series

**OBSOLETE** DATE: 08/21/202 PCN/ECN# 41356  
 REPLACED BY: P6SMB



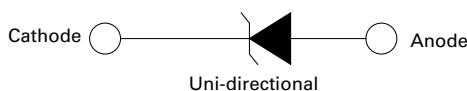
#### Maximum Ratings and Thermal Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Pulse Power Dissipation at $T_A = 25^\circ\text{C}$ by 10/1000μs Waveform (Fig.2)(Note 1), (Note 2)	$P_{PPM}$	600	W
Power Dissipation on Infinite Heat Sink at $T_L = 50^\circ\text{C}$	$P_D$	5.0	W
Peak Forward Surge Current, 8.3ms Single Half Sine Wave (Note 3)	$I_{FSM}$	100	A
Maximum Instantaneous Forward Voltage at 50A for Unidirectional Only	$V_F$	3.5	V
Operating Temperature Range	$T_J$	-65 to 150	°C
Storage Temperature Range	$T_{STG}$	-65 to 175	°C
Typical Thermal Resistance Junction to Lead	$R_{JL}$	20	°C/W
Typical Thermal Resistance Junction to Ambient	$R_{JA}$	100	°C/W

**Notes:**

1. Non-repetitive current pulse , per Fig. 4 and derated above  $T_J$  (initial) =  $25^\circ\text{C}$  per Fig. 3.
2. Mounted on copper pad area of  $0.2 \times 0.2"$  ( $5.0 \times 5.0\text{mm}$ ) to each terminal.
3. Measured on 8.3ms single half sine wave or equivalent square wave for unidirectional device only, duty cycle=4 per minute maximum.

#### Functional Diagram



#### Description

The P6SMB-E series is designed specifically to protect sensitive electronic equipment from voltage transients induced by lightning and other transient voltage events.

#### Features

- Excellent clamping capability
- Low incremental surge resistance
- For surface mounted applications to optimize board space
- Low profile package
- Typical failure mode is short from over-specified voltage or current
- Whisker test is conducted based on JEDEC JESD201A per its table 4a and 4c
- IEC 61000-4-2 ESD 30kV(Air), 30kV (Contact)
- EFT protection of data lines in accordance with IEC 61000-4-4
- Built-in strain relief
- Fast response time: typically less than 1.0ps from 0V to BV min
- 600W peak pulse power capability at 10/1000μs waveform, repetition rate (duty cycles):0.01 %
- High temperature to reflow soldering guaranteed:  $260^\circ\text{C}/40\text{sec}$
- $V_{BR} @ T_J = V_{BR} @ 25^\circ\text{C} \times (1 + \alpha T \times (T_J - 25))$  ( $\alpha$ :T:Temperature Coefficient, typical value is 0.1%)
- EPI silicon technology
- Meet MSL level1, per J-STD-020C, LF maximum peak of  $260^\circ\text{C}$
- Matte tin lead-free plated
- Halogen free and RoHS compliant
- Pb-free E3 means 2nd level interconnect is Pb-free and the terminal finish material is tin(Sn) (IPC/JEDEC J-STD-609A.01)

#### Applications

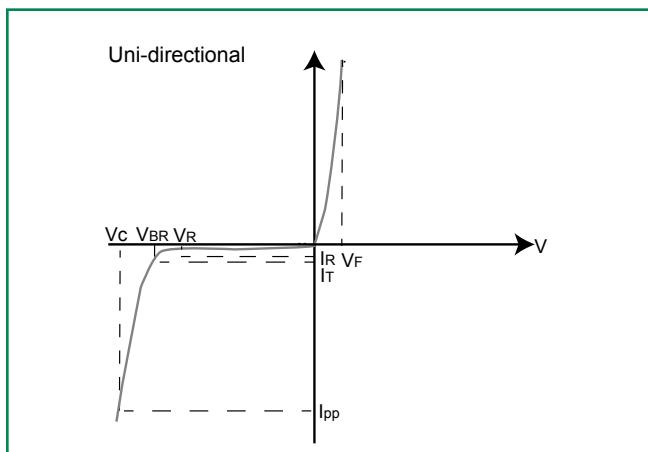
TVS devices are ideal for the protection of I/O Interfaces,  $V_{cc}$  bus and other vulnerable circuits used in Telecom, Computer, Industrial and Consumer electronic applications.

### Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Part Number (Uni)	Marking	Reverse Stand off Voltage $V_R$ (Volts)	Breakdown Voltage $V_{BR}$ (Volts) @ $I_T$		Test Current $I_T$ (mA)	Maximum Clamping Voltage $V_c$ @ $I_{pp}$ (V)	Maximum Peak Pulse Current $I_{pp}$ (A)	Maximum Reverse Leakage $I_R$ @ $V_R$ ( $\mu\text{A}$ )
			MIN	MAX				
P6SMB350A-E	350S	300	332.0	368.0	1	482.0	1.30	1
P6SMB400A-E	400S	342	380.0	420.0	1	548.0	1.10	1
P6SMB440A-E	440S	376	418.0	462.0	1	602.0	1.00	1
P6SMB480A-E*	480S	408	456.0	504.0	1	658.0	0.95	1
P6SMB510A-E*	510S	434	485.0	535.0	1	698.0	0.86	1
P6SMB530A-E*	530S	451	503.5	556.5	1	725.0	0.83	1
P6SMB540A-E*	540S	460	513.0	567.0	1	740.0	0.82	1
P6SMB550A-E*	550S	468	522.5	577.5	1	760.0	0.79	1
P6SMB600A-E*	600S	510	570.0	630.0	1	822.0	0.73	1
P6SMB650A-E*	650S	553	617.5	682.5	1	891.0	0.68	1
P6SMB700A-E*	700S	595	665.0	735.0	1	959.0	0.63	1
P6SMB800A-E*	800S	680	760.0	840.0	1	1096.0	0.55	1
P6SMB900A-E*	900S	765	855.0	945.0	1	1233.0	0.50	1
P6SMB1000A-E*	1000S	850	950.0	1050.0	1	1365.0	0.44	1

Note: for parts with \* are still under development

### I-V Curve Characteristics



**P<sub>PPM</sub>** **Peak Pulse Power Dissipation** – Max power dissipation

**V<sub>R</sub>** **Stand-off Voltage** – Maximum voltage that can be applied to the TVS without operation

**V<sub>BR</sub>** **Breakdown Voltage** – Maximum voltage that flows through the TVS at a specified test current ( $I_T$ )

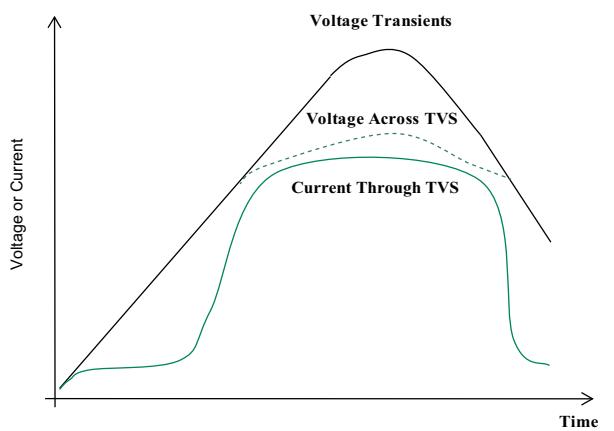
**V<sub>c</sub>** **Clamping Voltage** – Peak voltage measured across the TVS at a specified  $I_{ppm}$  (peak impulse current)

**I<sub>R</sub>** **Reverse Leakage Current** – Current measured at  $V_R$

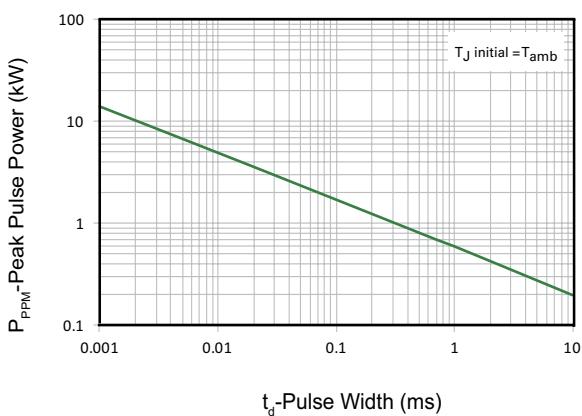
**V<sub>F</sub>** **Forward Voltage Drop for Uni-directional**

**Ratings and Characteristic Curves ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

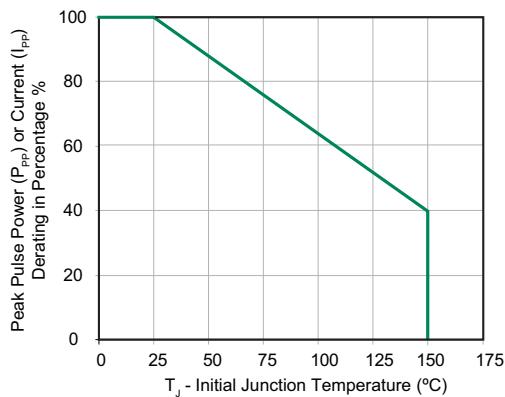
**Figure 1 - TVS Transients Clamping Waveform**



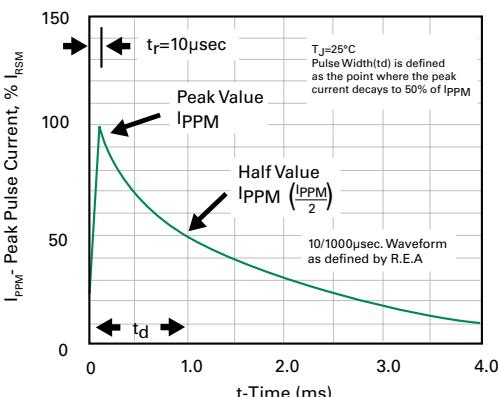
**Figure 2 - Peak Pulse Power Rating**



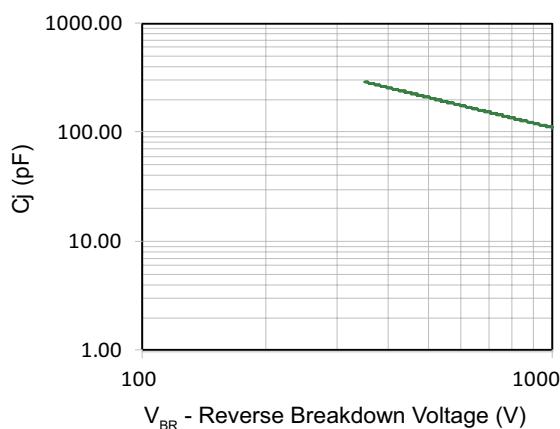
**Figure 3 - Peak Pulse Power Derating Curve**



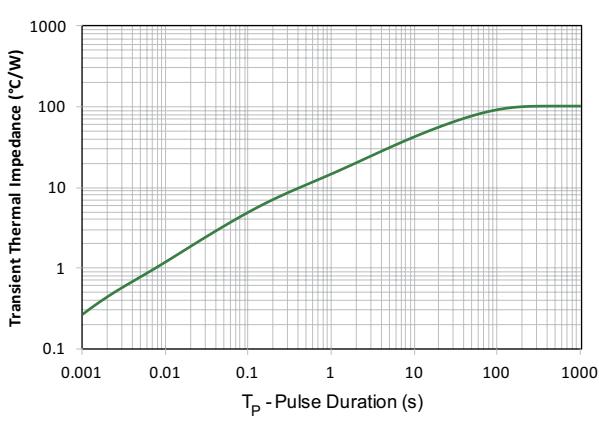
**Figure 4 - Pulse Waveform**



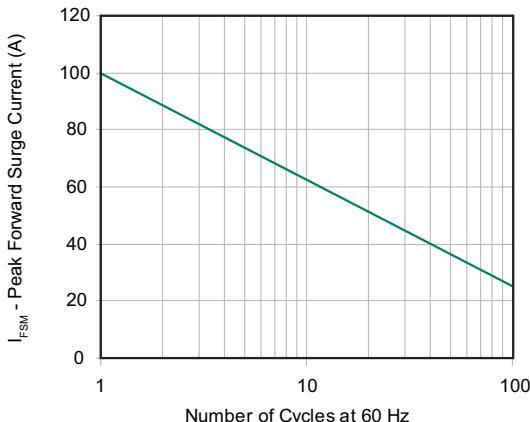
**Figure 5 - Typical Junction Capacitance**



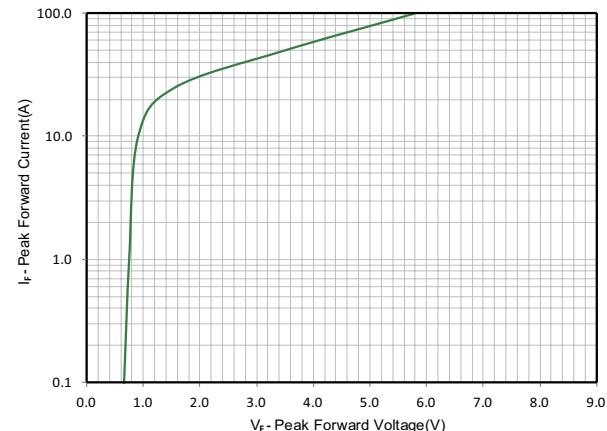
**Figure 6 - Typical Transient Thermal Impedance**



**Figure 7 - Maximum Non-Repetitive Peak Forward Surge Current Uni-Directional Only**

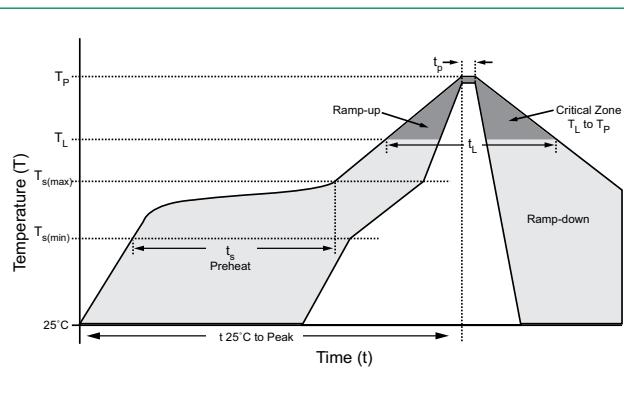


**Figure 8 - Peak Forward Voltage Drop vs Peak Forward Current (Typical Values)**



### Soldering Parameters

Reflow Condition		Lead-free assembly
Pre Heat	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus Temp ( $T_A$ ) to peak		3°C/second max
$T_{s(max)}$ to $T_A$ - Ramp-up Rate		3°C/second max
Reflow	- Temperature ( $T_A$ ) (Liquidus)	217°C
	- Time (min to max) ( $t_s$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		260°C



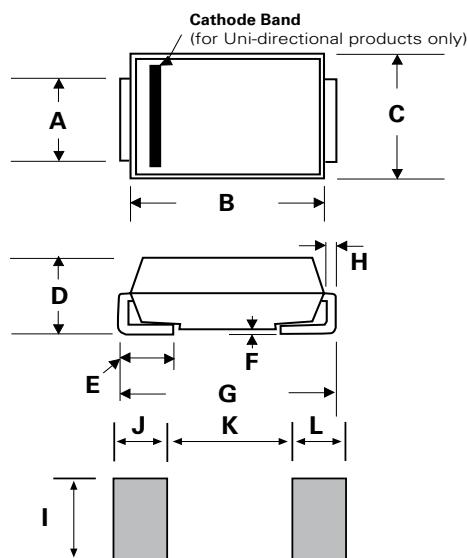
### Physical Specifications

<b>Weight</b>	0.003 ounce, 0.093 grams
<b>Case</b>	JEDEC DO214AA. Molded plastic body over glass passivated junction
<b>Polarity</b>	Color band denotes cathode except Bidirectional
<b>Terminal</b>	Matte Tin-plated leads, Solderable per JESD22-B102

### Environmental Specifications

<b>High Temp. Storage</b>	JESD22-A103
<b>HTRB</b>	JESD22-A108
<b>Temperature Cycling</b>	JESD22-A104
<b>MSL</b>	JEDEC-J-STD-020, Level 1
<b>H3TRB</b>	JESD22-A101
<b>RSH</b>	JESD22-A111

### Dimensions

**DO-214AA (SMB J-Bend)**


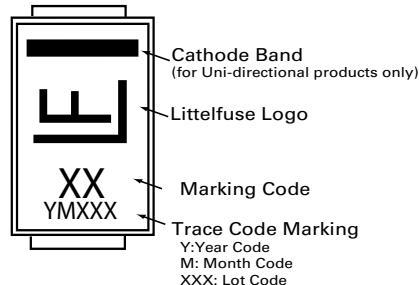
Dimensions	Inches		Millimeters	
	Min	Max	Min	Max
A	0.076	0.086	1.930	2.200
B	0.160	0.187	4.060	4.750
C	0.130	0.155	3.300	3.940
D	0.078	0.103	1.990	2.610
E	0.030	0.060	0.760	1.520
F	-	0.008	-	0.203
G	0.205	0.220	5.210	5.590
H	0.006	0.012	0.152	0.305
I	0.089	-	2.260	-
J	0.085	-	2.160	-
K	-	0.107	-	2.740
L	0.085	-	2.160	-

### Part Numbering System

P6SMB xxx A-E

- EPI SILICON TECHNOLOGY
- 5% V<sub>BR</sub> VOLTAGE TOLERANCE
- V<sub>BR</sub> VOLTAGE
- SERIES

### Part Marking System



### Packaging

Part number	Component Package	Quantity	Packaging Option	Packaging Specification
P6SMBxxxA-E	DO-214AA	3000	Tape & Reel - 12mm tape/13" reel	EIA STD RS-481

### Tape and Reel Specification

